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	AA	10/443,335	Forbes			05/21/2003
	AB					
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	AM					
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Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-2272	SERIAL NO. Filed Herewith
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)					
	AA	S.S.K. Iyer et al., "Separation by Plasma Implantation of Oxygen (SPIMOX) operational phase space," IEEE Trans. On Plasma Science, Vol. 25, No. 5, pp. 1128-1135, 1997			
	AB	G.A. Garcia et al, High Quality in Thin (100nm) Silicon on Sapphire," IEEE Trans Electron Devices vol. no. 9, no. 1, pp. 32-34, Jan. (1988)			
	AC	E. Carugean, G. Garcia, G. Inshun, G. Kelley, H. Walker and L. Forbes, "Bonded Etchback Silicon on Sapphire Bipolar Junction Transistors," Abstracts of ECS meeting, May 1993, Honolulu, Hawaii, P. 1199.			
	AD	G.P. Imthurn, G.A. Garcia, H.W. Walker, and L. Forbes, "Bonded Silicon-On-Sapphire Wafers and Devices," J. Appl. Phys., 72(6), 15 September 1992, pp. 2526-2527			
	AE	P. Ball, "A Small Mountain of Materials Goes into Every Microchip," Nature Science Update, 19 Nov. 2002, http://www.nature.com/news/210208/021028-12.html			
	AF	"Materials Selector", Reinhold Publishing Co., Pearson/IPC. http://www.handyharmonic.com/TheBrazingBook/comparis.htm 12/02			
	AG	Company page http://www.hithermal.com/datasheets/index.cfm?pages=values 12/02			
	AH	R. People et al, "Calculation of Critical Layer Thickness Versus Lattice Mismatch for Ge ₂ Si ₃ /Si Strained Layer Heterostructures," Appl. Phys. Letters, Vol. 47, p. 3223-324, August 1985.			
	AI	R. People et al, "Erratum: Calculation of Critical Layer Thickness Versus Lattice Mismatch for Ge ₂ Si ₃ /Si Strained Layer Heterostructures," Appl. Phys. Letters, Vol. 49, P. 229, July 1986.			
	AJ	G. Orenet et al., "Testing the Feasibility of Strain Relaxed Compliant Substrates," Abstract of Electronic Materials Conference, Santa Barbara, June 2002, P.8.			
	AK	K.D. Hobart et al, "High Ge-Content Relaxed SiGe Layers by Relaxation on Compliant Substrate with Controlled Oxidation," Abstract of Electronic Materials Conference, Santa Barbara, June 2002, pp. 8.			
	AL	P. Moren et al., "Strain Relaxation in Wafer-bonded SiGe/Si Heterostructures Due to the Viscous Flow of an Underlying Borosilicate Glass," Abstract of Electronic Materials Conference, Santa Barbara, June 2002, pp. 8-9			
	AM	A.J. Auberton-Herve, "SOI: Materials to Systems," Digest of the International Electron Device Meeting, San Francisco, December 1996, pp. 5-10			
	AN	T. Tsuchida et al., "Self-combustion Reaction Induced by Mechanical Activation of Al-si-c Powder Mixtures," European Journal of Solid State and Inorganic Chemistry (France), Vol. 32, No. 7-8, pp. 629-38, 1995.			
	AO	H.C. Yu, et al, "Combustion Synthesis of Aluminoborate Glass Matrices," J. Mater. Synth. Process. (USA), Vol. 8, No. 1, pp. 15-20, Jan. 2000.			
	AP	Dip.-Ing. M. Wild, Dr.-Ing. A. Giltner, "Laser Assisted Bonding of Silicon and Glass in Micro-System Technology," 07/03 http://www.ilt.fhg.de/esg/b00-e42.html			
	AQ	Saman Dharmatileke et al, "Anodic Bonding of Glass to Glass and Silicon to Glass or Silicon to Silicon Through a Very Thick Thermally Grown SiO ₂ Layer," Proceedings of ISMI International Symposium on Smart Structures & Microsystems, Hong Kong, October 19-21, 2000, p. 32. http://dsulphin.eng.us.edu/projects/bonding/paper.pdf			
	AR				
	AS				
	AT				
	AU				
Examiner		/Long Pham/ (02/29/2008)		Date Considered	
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